•				o Lamb	W	Det Tilt CTOH	ĸ
	5311	((gate near5 source)near5 capacit\$4)	USPA T	2001/10/2 4 12:26		0	٦
5 L2	3481	(pcwer adj2 mosfet)	USPA T	2001/10/2 4 13:11	1	0	J
5 L3	29382	poly same (ins or silicon adj dioxide or oxi	USPA T	2001/10/2 4 13:11		0	J
5 L4	112	diffusion near3 (source and channel)	USPA T	1/10/ 3:12		0	J
6 L5	9144	ate same (tr rocv\$3)	USPA T	001/1 13:2		0	<u> </u>
S L6	0	ard nd 5	USPA T	1/1 1:4		0	
s L7	Н	1 ar.d 2 and 3 and 5	USPA T				0
S L8	46	2 and 3 and 5	USPA T				0
s L9	115	((gate near5 source)near5 capacit\$4)	US-P GPUB	2001/10/2 4 12:39		(	0
H H	) 74	(power adj2 mosfet)	US-P GPUB	2001/10/2 4 12:39		(	0
H H	545	<pre>poly same (insulat\$5 or silicon adj2 dioxide or oxide)</pre>	US-P GPUB	9		(	0
L1	3 342	gate same (trench or groov\$3)	US-P GPUB	001/10/ 12:39		(	0
Ľ	2	diffusion near3 (source and channel)	US-P GPUB	001/10/ 12:39		(	0
Ľ1	0	9 and 10 and 11 and 13	S-	001/10/ 12:28			0
멑	0	9 and 11 and 13	DQ -S	001/10/ 12:29		(	0
Ľ1	7 13	11 and 13 and MOSFET	US-P GPUB	1/ 2:			0
	L1 L1 L2 L2 L3 L3 L3 L3 L1 L1 L1 L1 L1 L1	L1 5311 L2 3481 L2 3481 L3 2938 L3 2938 L5 9144 L5 9144 L6 0 L6 0 L17 1 L11 545 L11 545 L11 545 L11 0 L11 0	L1 5311 source) near5 L1 5311 source) near5 L2 3481 (pcwer adj2 mosfet) poly same (insulat\$5 L3 29382 or silicon adj2 dioxide or oxide) L5 9144 gate same (trench or grocv\$3) L7 1 1 ard 2 and 3 and 4 L6 0 and 5 L8 46 2 and 3 and 5 L9 115 source) near5 L9 115 source) near5 L9 115 source) near5 L11 545 or silicon adj2 mosfet) poly same (insulat\$5 or silicon adj2 dioxide or oxide) poly same (trench or gate same) L11 0 9 and 10 and 11 and 13 L11 13 11 and 13 and MOSFE	L1 5311 source) near5 L2 3481 (pcwer adj2 mosfet) T L3 29382 or silicon adj2 diffusion near3 L4 112 (diffusion near3 channel) T L5 9144 grocv\$3) L6 0 lard 2 and 3 and 4 T L7 1 lard 2 and 3 and 5 T L8 46 2 and 3 and 5 T L9 115 source) near5 L9 115 source) near5 L9 115 source) near5 L10 74 (pcwer adj2 mosfet) GP L11 545 or silicon near3 L12 4 (source and channel) GP L11 0 9 and 10 and 11 and GP L11 13 342 grocv\$3) L12 4 (source and channel) GP L13 342 grocv\$3) L14 0 9 and 11 and 13 GP L15 0 9 and 11 and 13 GP	L1 5311 source)near5 L2 3481 (pcwer adj2 mosfet) T 4 12:26 L2 3481 (pcwer adj2 mosfet) T 4 13:11 L3 29382 or silicon adj2 L4 112 (source and channel) T 4 13:12 L5 9144 (procv\$3) L6 0 1 ard 2 and 3 and 4 USPA 2001/10/10/10/10/10/10/10/10/10/10/10/10/	L1 5311 Source)near5 L2 3481 (pcwer adj2 mosfet) T 4 12:26 L2 3481 (pcwer adj2 mosfet) T 4 13:11 L3 29382 poly same (insulat\$5 USPA 2001/10/2 diffusion near3 USPA 2001/10/2 T 4 13:11 L4 112 diffusion near3 USPA 2001/10/2 T 4 13:12 L5 9144 grocv\$3) L6 0 1 ard 2 and 3 and 4 USPA 2001/10/2 T 4 11:42 L7 1 1 1 ard 2 and 3 and 5 T 4 11:42 L8 46 2 and 3 and 5 T 4 11:42 L9 115 Source)near5 L10 74 (power adj2 mosfet) USPA 2001/10/2 C 2001/10/2	L1   S311   SOUTCE   near5   USPA   2001/10/2

0			2001/10/2	JPO	28 and 29 and 30 and 31 and 32.	. 0	L33	BRS	32
0		2	1/10/ 3:03	JPO	gate same (trench or groov\$3)	4398	L31	BRS	3 1
0			2001/10/2 4 12:47	JРО	(power adj2 mosfet)	635	L30	BRS	30
0			2001/10/2 4 12:47	JPO	poly same (insulat\$5 or silicon adj2 dioxide or oxide)	4122	L29	BRS	29
0		2	2001/10/2 4 13:04	JРО	((gate near5 source)near5 capacit\$4)	1009	L28	BRS	28
0			2001/10/2 4 12:42	EPO	20 and 21	16	L27	BRS	27
0			2001/10/2 4 12:41	EPO	18 and 19	0	L26	BRS	26
0			0/ 1	EPO	19 and 20	5	L25	BRS	25
0			10/	EPO	18 and 19 and 20	0	L24	BRS	24
0			20	EPO	18 and 19 and 20 and 21	0	L23	BRS	23
0			001/10/ 12:48	EPO	<pre>diffusion near3 (source and channel)</pre>	2	L22	BRS	22
0			001/10/ 12:48	EPO	gate same (trench or groov\$3)	1247	L21	BRS	21
0			2001/10/2 4 12:47	EPO	<pre>poly same (insulat\$5 or silicon adj2 dioxide or oxide)</pre>	1420	L20	BRS	20
0			2001/10/2 4 12:47	EPO	(power adj2 mosfet)	406	L19	BRS	19
0			2001/10/2 4 12:47	EPO	((gate near5 source)near5 capacit\$4)	280	L18	BRS	18
0			2001/10/2 4 12:33	US-P GPUB	11 and 13	58	L16	BRS	17
H O H	Error Definition	Comment	Time Stamp	DBs	Search Text	Hits	# #	Туре	

0			2001/10/2	DERW	44 and 46 and diffusion	31	L54	BRS	54
0				DERW ENT	44 and 46	161	L53	BRS	53
0			001/	DERW	43 and 44 and 46	ш	L52	BRS	52
0			001/1 13:2	DERW	gate same (trench or groov\$3)	4093	L46	BRS	46
0			001/ 13:	DERW	diffusion near3 (source and channel)	13	L45	BRS	45
0			2001/10/2 4 13:12	DERW ENT	poly same (insulat\$5 or silicon adj2 dioxide or oxide)	15407	L44	BRS	44
0			2001/10/2 4 13:11	DERW ENT	(power adj2 mosfet)	1448	L43	BRS	43
0			1/ 3:	JPO	28 and 29	10	L42	BRS	42
0			2001/10/2 4 13:04	DERW ENT	((gate near5 source)near5 capacit\$4)	1031	L41	BRS	41
0			2001/10/2 4 13:03	JPO	gate same (poly and trench or groov\$3)	3403	L40	BRS	40
0			001/ 12:	JPO	29 and 31 and poly	84	L39	BRS	39
0			001/10/ 12:52	JРО	29 and 31	84	L38	BRS	38
0			001/ 12:	JPO	29 and 30 and 31	0	L37	BRS	37
0			001/1 13:0	JPO	28 and 29 and 30 and 31	0	L36	BRS	36
0			2001/10/2 4 12:50	JPO	29 and poly	4122	L35	BRS	35
0			001/ 12:	JPO	29 and 32	0	L34	BRS	34
0			001/1 12:4	JPO	diffusion near3 (source and channel)	11	L32	BRS	ω ω
Er ro	Error Definition	Comment	Time Stamp	DBs	Search Text	Hits	۲ #	Туре	